

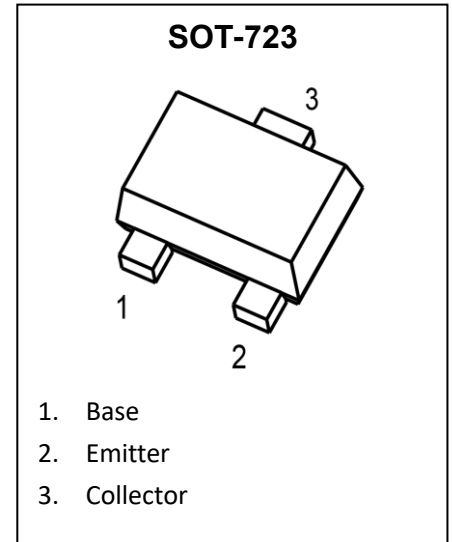
**MMBT2222AM Transistor(NPN)**
**Features:**

- Epitaxial Planar Die Construction

**Marking:** 1P

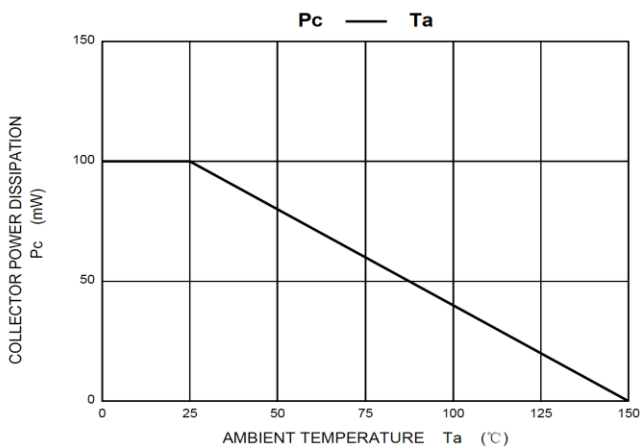
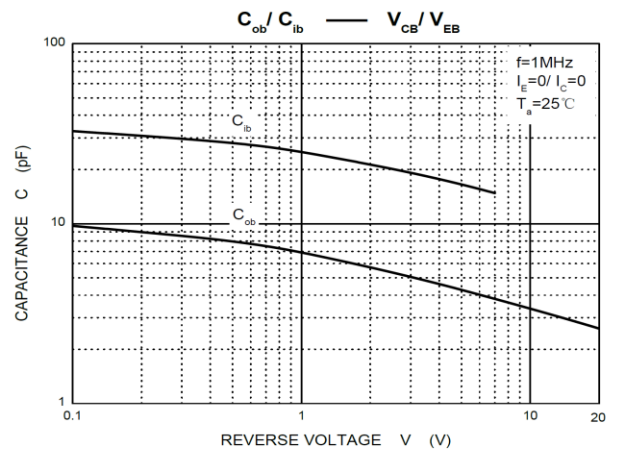
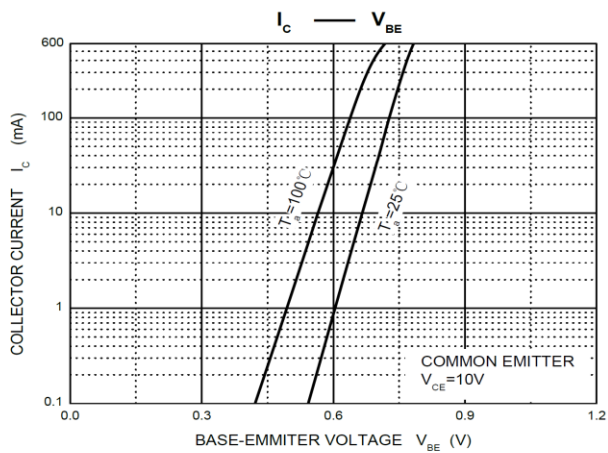
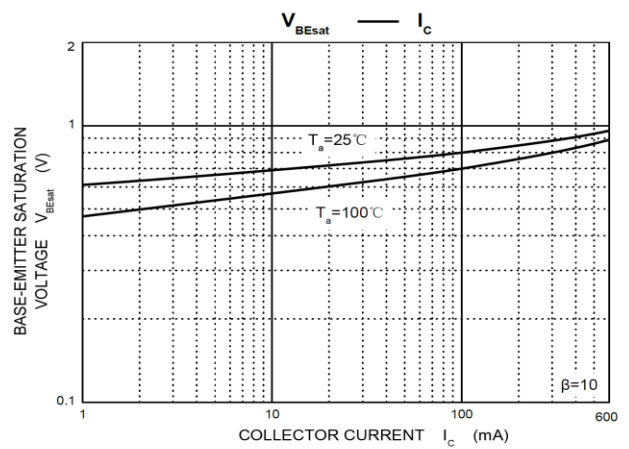
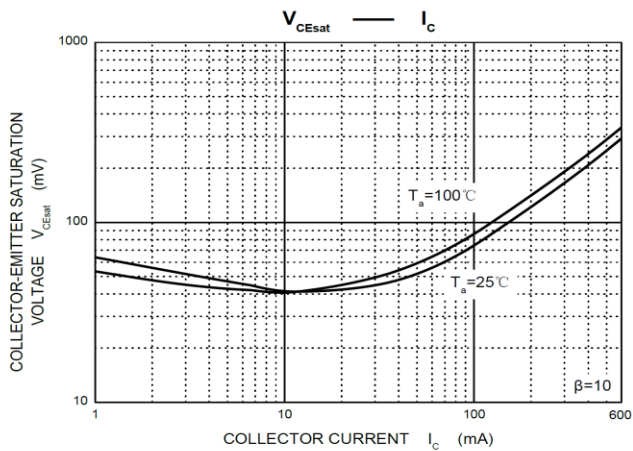
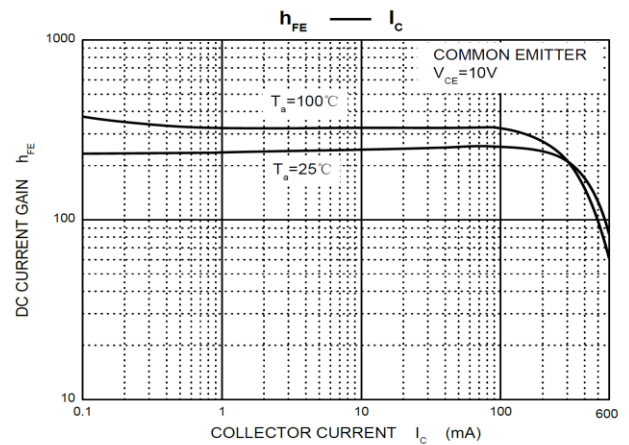
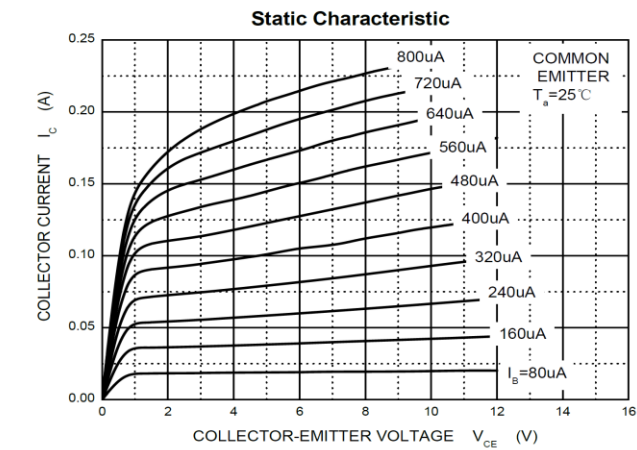
**MAXIMUM RATINGS (T<sub>A</sub> = 25°C unless otherwise noted)**

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	75	V
Collector-Emitter Voltage	V <sub>CEO</sub>	40	V
Emitter-Base Voltage	V <sub>EBO</sub>	6	V
Collector Current -Continuous	I <sub>C</sub>	0.5	A
Power Dissipation	P <sub>d</sub>	0.1	W
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature	T <sub>STG</sub>	-55~ +150	°C

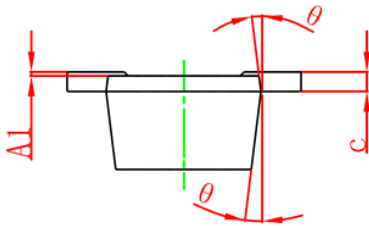
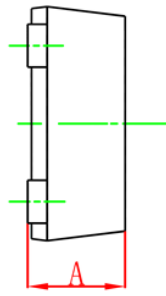
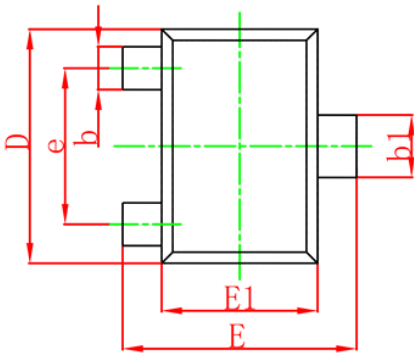

**ELECTRICAL CHARACTERISTICS(T<sub>A</sub> = 25°C unless otherwise noted)**

Parameter	Symbol	Test Condition	Min	Max	Unit
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> = 10μA, I <sub>E</sub> = 0	75		V
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> = 10mA, I <sub>B</sub> = 0	40		V
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> = 10μA, I <sub>C</sub> = 0	6		V
Collector Cut-Off Current	I <sub>CBO</sub>	V <sub>CB</sub> = 60V, I <sub>E</sub> = 0		10	nA
Collector Cut-Off Current	I <sub>CEX</sub>	V <sub>CE</sub> = 60V, V <sub>EB(off)</sub> = 3V		10	nA
Emitter Cut-Off Current	I <sub>EBO</sub>	V <sub>EB</sub> = 3V, I <sub>C</sub> = 0		10	nA
DC Current Gain	h <sub>FE1</sub>	V <sub>CE</sub> = 10V, I <sub>C</sub> = 0.1mA	40		
	h <sub>FE2</sub>	V <sub>CE</sub> = 10V, I <sub>C</sub> = 150mA	100	300	
	h <sub>FE3</sub>	V <sub>CE</sub> = 10V, I <sub>C</sub> = 500mA	42		
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = 150mA, I <sub>B</sub> = 15mA		0.3	V
		I <sub>C</sub> = 500mA, I <sub>B</sub> = 50mA		1	V
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> = 150mA, I <sub>B</sub> = 15mA		1.2	V
		I <sub>C</sub> = 500mA, I <sub>B</sub> = 50mA		2	V
Transition Frequency	f <sub>T</sub>	V <sub>CE</sub> = 20V, I <sub>C</sub> = 20mA, f = 100MHz	300		MHZ
Delay Time	t <sub>d</sub>	V <sub>CC</sub> = 30V, I <sub>C</sub> = 150mA,		10	ns
Rise Time	t <sub>r</sub>	V <sub>BE(off)</sub> = -0.5V, I <sub>B1</sub> = 15mA		25	ns
Storage Time	t <sub>s</sub>	V <sub>CC</sub> = 30V, I <sub>C</sub> = 150mA,		225	ns
Fall Time	t <sub>f</sub>	I <sub>B1</sub> = I <sub>B2</sub> = 15mA		60	ns

Typical Characteristics



## SOT-723 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
<b>A</b>	0.340	0.500	0.013	0.020
<b>A1</b>	0.000	0.050	0.000	0.002
<b>b</b>	0.150	0.270	0.006	0.011
<b>b1</b>	0.200	0.370	0.008	0.015
<b>c</b>	0.060	0.160	0.002	0.006
<b>D</b>	1.100	1.300	0.043	0.051
<b>E</b>	1.100	1.300	0.043	0.051
<b>E1</b>	0.700	0.900	0.028	0.035
<b>e</b>	0.8TYP		0.031TYP	
<b><math>\theta</math></b>	8°REF		8°REF	

**Attention:**

- GreenPower Electronics reserves the right to improve product design function and reliability without notice.
- Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.
- GreenPower Electronics products belong to consumer electronics or other civilian electronic products.